

## FNK N-Channel Enhancement Mode Power MOSFET

### Description

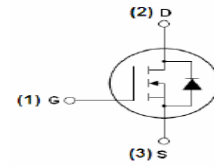
The FNK01N15D uses advanced trench Technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge .It can be used in a wide variety of applications

### General Features

- $V_{DS} = 100V, I_D = 150A$   
 $R_{DS(ON)} < 5.7m\Omega @ V_{GS}=10V$
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation
- Good stability and uniformity with high EAS

### Application

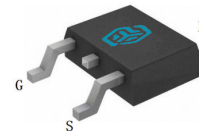
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



Marking and pin Assignment



TO-263 top view

### PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FNK01N15D	FNK01N15D	TO-263	-	-	-

### ABSOLUTE MAXIMUM RATINGS( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D(25^\circ C)$	150	A
	$I_{DM}$	600	A
Maximum Power Dissipation	$P_D$	375	W
Single pulse avalanche energy(Note 5)	EAS	433	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

### THERMAL CHARACTERISTICS

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	0.4	$^\circ C/W$
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### ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						

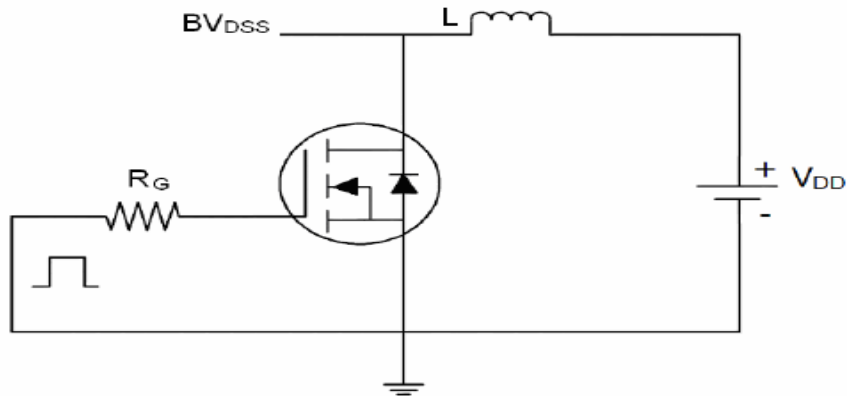
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	100	110		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2	2.8	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		5.0	5.7	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =20A	70			S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, F=1.0MHz		6470		PF
Output Capacitance	C <sub>oss</sub>			690		PF
Reverse Transfer Capacitance	C <sub>rss</sub>			430		PF
SWITCHING CHARACTERISTICS (Note 4)						
Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =50V, V <sub>GS</sub> =10V, R <sub>GEN</sub> =3Ω I <sub>D</sub> =2A RL=2.5Ω		28		nS
Turn-on Rise Time	t <sub>r</sub>			22		nS
Turn-Off Delay Time	t <sub>d(off)</sub>			43.5		nS
Turn-Off Fall Time	t <sub>f</sub>			14.5		nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =50V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V		139		nC
Gate-Source Charge	Q <sub>gs</sub>			34		nC
Gate-Drain Charge	Q <sub>gd</sub>			56		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A		0.85	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>				160	A
Reverse Recovery Time	trr	T <sub>J</sub> = 25℃, I <sub>F</sub> = 20A di/dt = 500A/us(Note3)		60	90	nS
Reverse Recovery Charge	Qrr			177	200	nC

## NOTES:

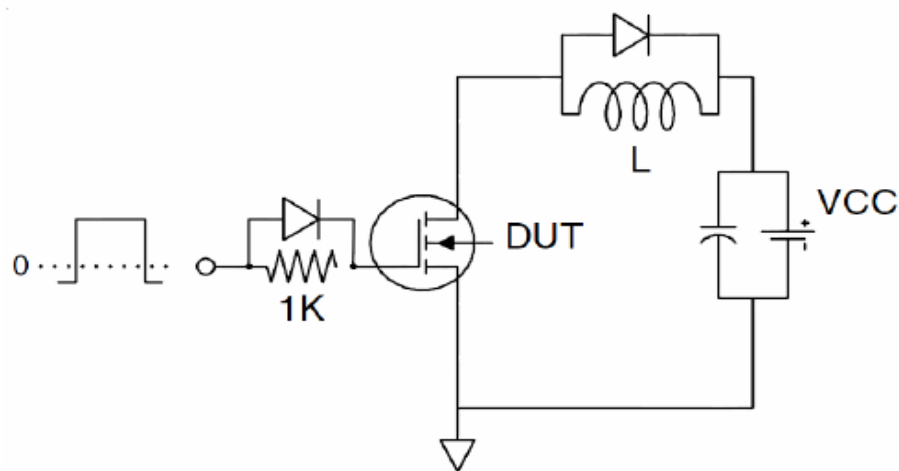
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in<sup>2</sup> FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing
5. EAS condation:  $T_J=25^\circ C, V_{dd}=20V, V_g=10V, L=0.5mH, R_g=25\Omega$

## Test circuit

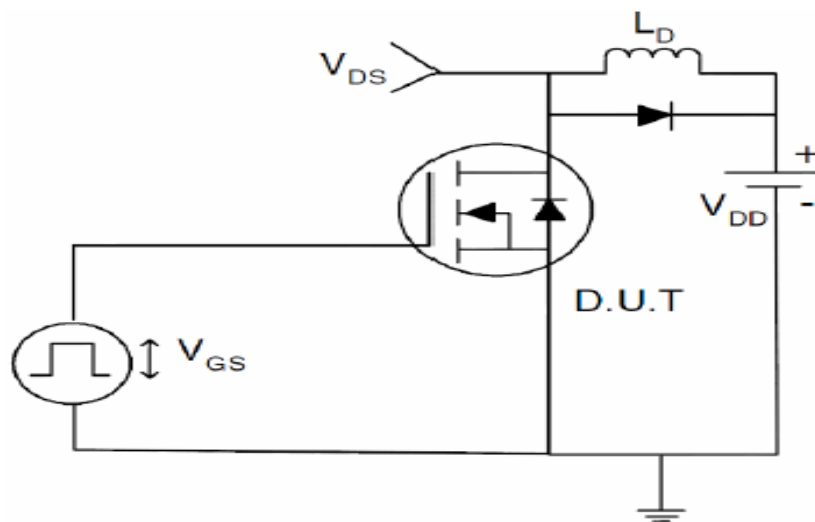
### 1) EAS Test Circuit



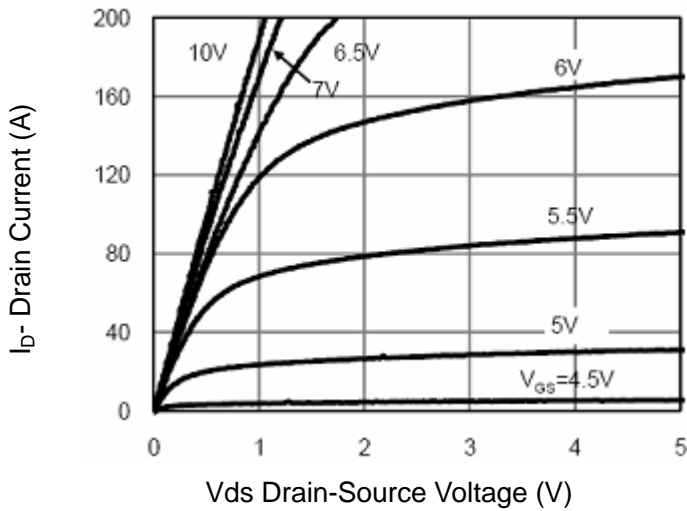
### 2) Gate Charge Test Circuit



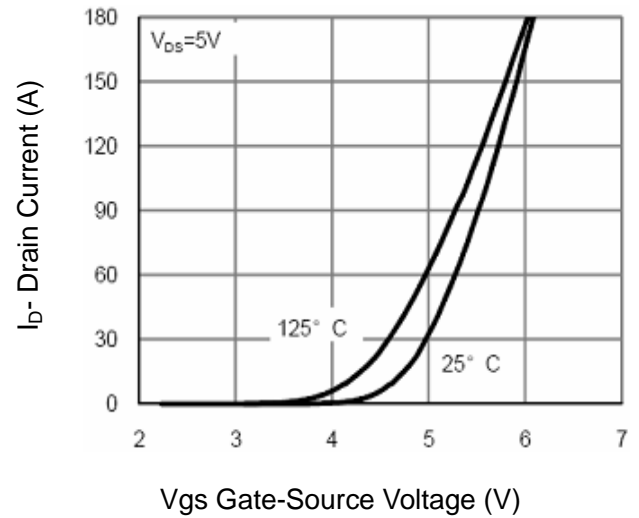
### 3) Switch Time Test Circuit



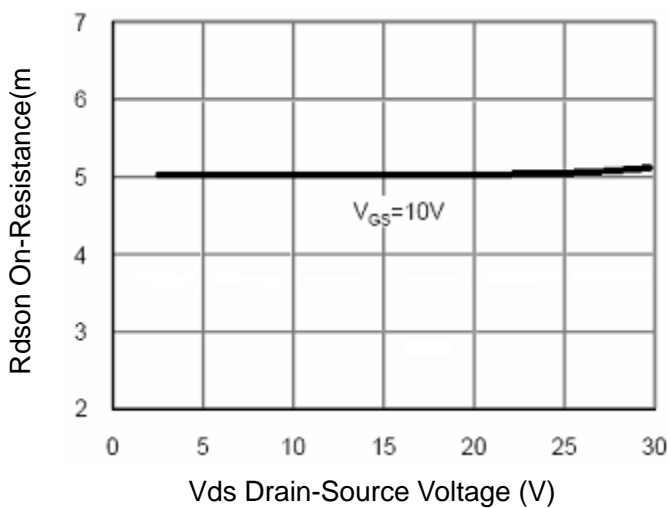
## Typical Electrical and Thermal Characteristics (Curves)



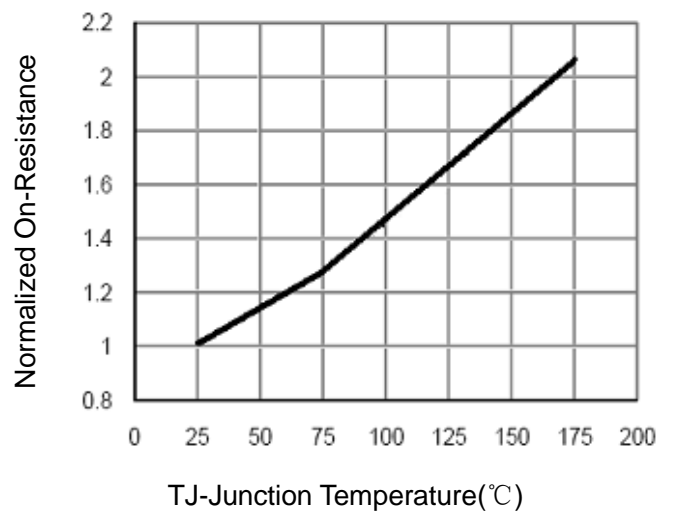
**Figure 1 Output Characteristics**



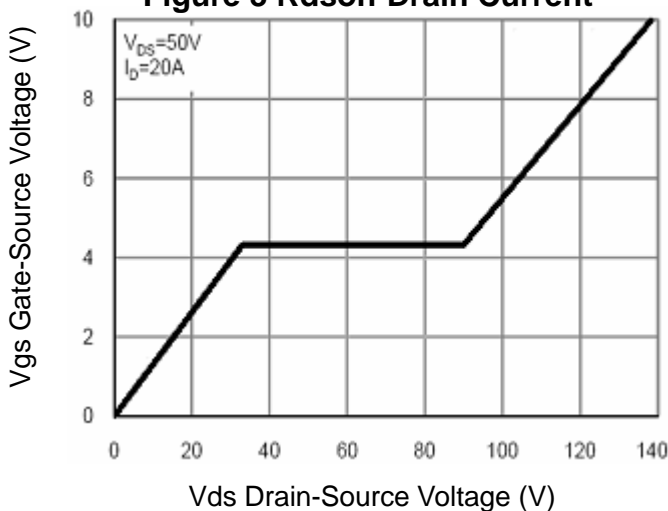
**Figure 2 Transfer Characteristics**



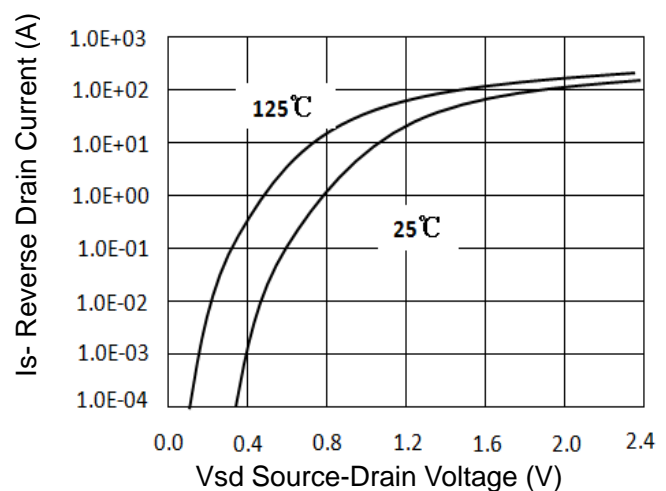
**Figure 3 Rdson-Drain Current**



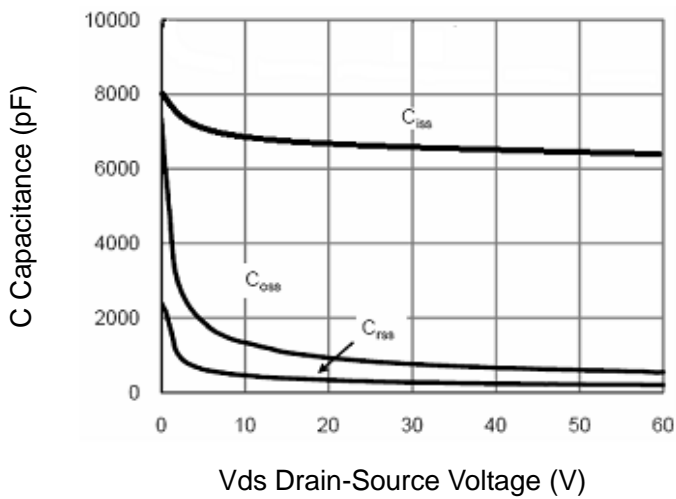
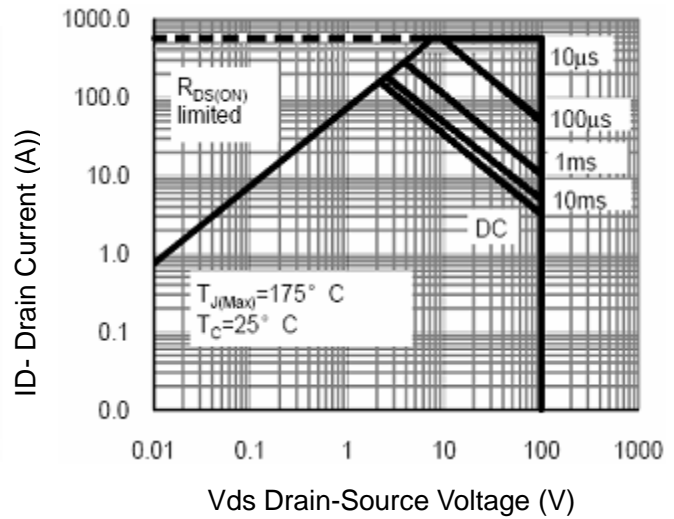
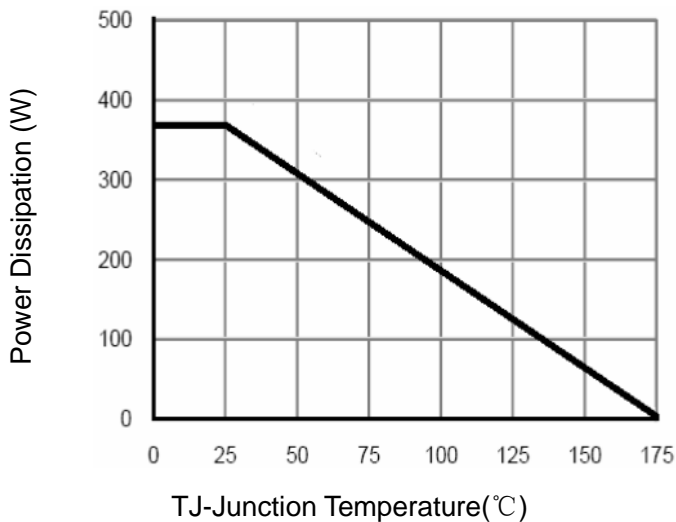
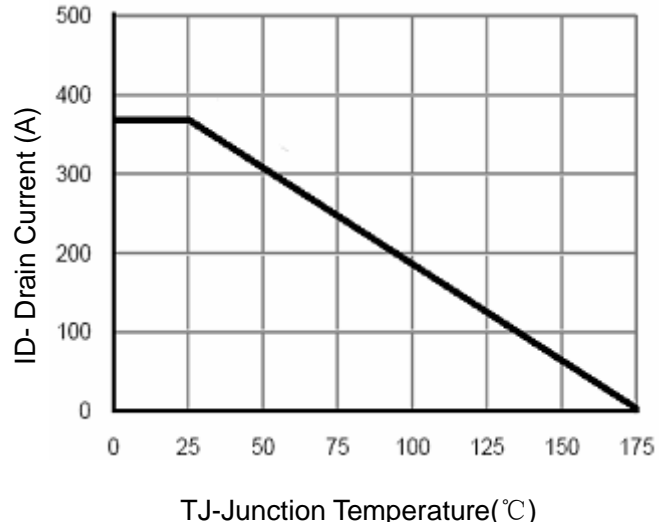
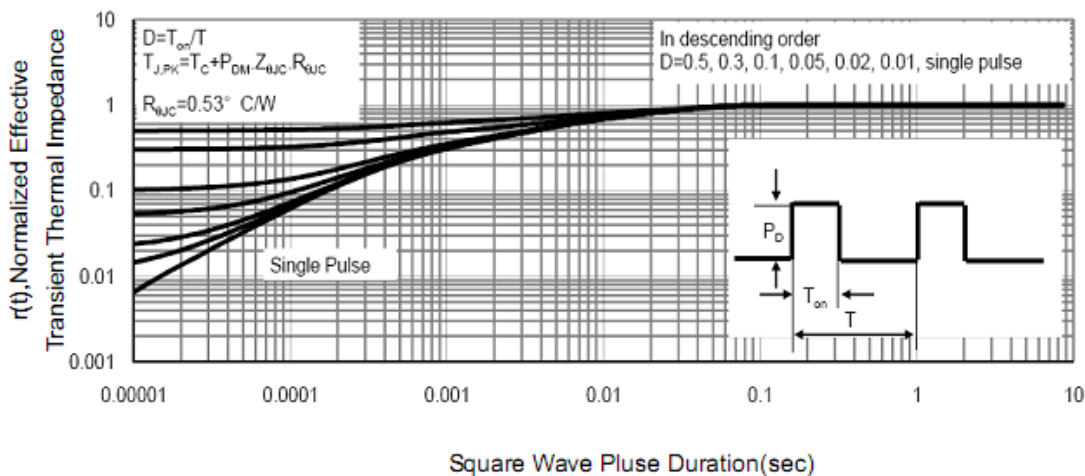
**Figure 4 Rdson-Junction Temperature**



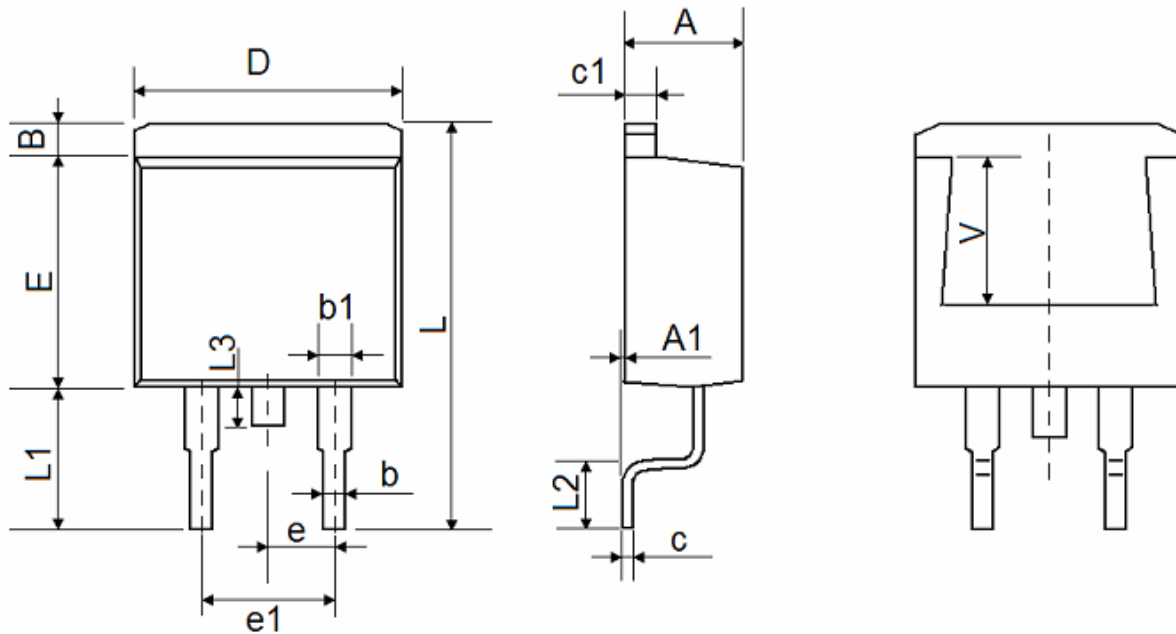
**Figure 5 Output CHARACTERISTICS**



**Figure 6 Source- Drain Diode Forward**


**Figure 7 Capacitance vs Vds**

**Figure 8 Safe Operation Area**

**Figure 9 Power De-rating**

**Figure 10 Current De-rating**

**Figure 11 Normalized Maximum Transient Thermal Impedance**

## TO-263 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF		0.220 REF	

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